

MM54HC20/MM74HC20 Dual 4-Input NAND Gate

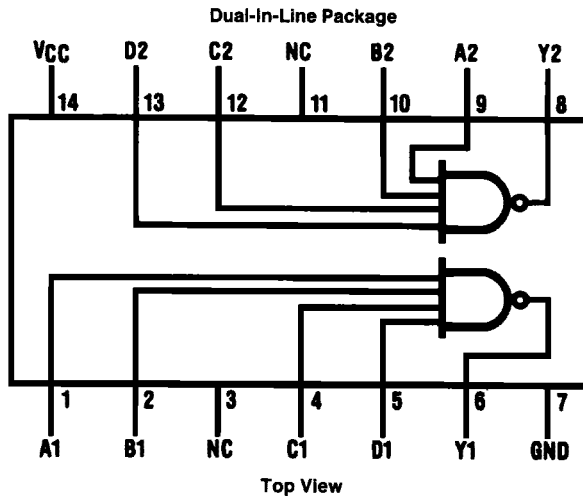
General Description

These NAND gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. All gates have buffered outputs. All devices have high noise immunity and the ability to drive 10 LS-TTL loads. The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 8 ns
- Wide power supply range: 2–6V
- Low quiescent current: 20 μ A maximum (74HC Series)
- Low input current: 1 μ A maximum
- Fanout of 10 LS-TTL loads

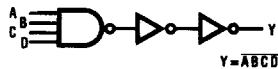
Connection and Logic Diagrams



TL/F/5299-1

Order Number MM54HC20* or MM74HC20*

*Please look into Section 8, Appendix D for availability of various package types.



TL/F/5299-2

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

| | |
|--|-------------------------|
| Supply Voltage (V_{CC}) | -0.5 to +7.0V |
| DC Input Voltage (V_{IN}) | -1.5 to $V_{CC} + 1.5V$ |
| DC Output Voltage (V_{OUT}) | -0.5 to $V_{CC} + 0.5V$ |
| Clamp Diode Current (I_{IK}, I_{OK}) | ± 20 mA |
| DC Output Current, per pin (I_{OUT}) | ± 25 mA |
| DC V_{CC} or GND Current, per pin (I_{CC}) | ± 50 mA |
| Storage Temperature Range (T_{STG}) | -65°C to +150°C |
| Power Dissipation (P_D) | |
| (Note 3) | 600 mW |
| S.O. Package only | 500 mW |
| Lead Temp. (T_L) (Soldering 10 seconds) | 260°C |

Operating Conditions

| | Min | Max | Units |
|--|-----|----------|-------|
| Supply Voltage (V_{CC}) | 2 | 6 | V |
| DC Input or Output Voltage (V_{IN}, V_{OUT}) | 0 | V_{CC} | V |
| Operating Temp. Range (T_A) | | | |
| MM74HC | -40 | +85 | °C |
| MM54HC | -55 | +125 | °C |
| Input Rise or Fall Times (t_r, t_f) | | | |
| $V_{CC} = 2.0V$ | | 1000 | ns |
| $V_{CC} = 4.5V$ | | 500 | ns |
| $V_{CC} = 6.0V$ | | 400 | ns |

DC Electrical Characteristics (Note 4)

| Symbol | Parameter | Conditions | V_{CC} | $T_A = 25^\circ C$ | | 74HC | 54HC | Units |
|----------|-----------------------------------|---|----------|--------------------|-------------------|-----------------------------|------------------------------|---------|
| | | | | | | $T_A = -40$ to $85^\circ C$ | $T_A = -55$ to $125^\circ C$ | |
| | | | | Typ | Guaranteed Limits | | | |
| V_{IH} | Minimum High Level Input Voltage | | 2.0V | | 1.5 | 1.5 | 1.5 | V |
| | | | 4.5V | | 3.15 | 3.15 | 3.15 | V |
| | | | 6.0V | | 4.2 | 4.2 | 4.2 | V |
| V_{IL} | Maximum Low Level Input Voltage** | | 2.0V | | 0.5 | 0.5 | 0.5 | V |
| | | | 4.5V | | 1.35 | 1.35 | 1.35 | V |
| | | | 6.0V | | 1.8 | 1.8 | 1.8 | V |
| V_{OH} | Minimum High Level Output Voltage | $V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$ | 2.0V | 2.0 | 1.9 | 1.9 | 1.9 | V |
| | | | 4.5V | 4.5 | 4.4 | 4.4 | 4.4 | V |
| | | | 6.0V | 6.0 | 5.9 | 5.9 | 5.9 | V |
| | | $V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0$ mA $ I_{OUT} \leq 5.2$ mA | 4.5V | 4.2 | 3.98 | 3.84 | 3.7 | V |
| | | | 6.0V | 5.7 | 5.48 | 5.34 | 5.2 | V |
| | | | | | | | | |
| V_{OL} | Maximum Low Level Output Voltage | $V_{IN} = V_{IH}$ $ I_{OUT} \leq 20 \mu A$ | 2.0V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | | 4.5V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | | 6.0V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | $V_{IN} = V_{IH}$ $ I_{OUT} \leq 4.0$ mA $ I_{OUT} \leq 5.2$ mA | 4.5V | 0.2 | 0.26 | 0.33 | 0.4 | V |
| | | | 6.0V | 0.2 | 0.26 | 0.33 | 0.4 | V |
| | | | | | | | | |
| I_{IN} | Maximum Input Current | $V_{IN} = V_{CC}$ or GND | 6.0V | | ± 0.1 | ± 1.0 | ± 1.0 | μA |
| I_{CC} | Maximum Quiescent Supply Current | $V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$ | 6.0V | | 2.0 | 20 | 40 | μA |

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V $\pm 10\%$ the worst case output voltages (V_{OH} , and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{O2}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC}=5V, T_A=25^{\circ}C, C_L=15\text{ pF}, t_r=t_f=6\text{ ns}$

| Symbol | Parameter | Conditions | Typ | Guaranteed Limit | Units |
|--------------------|---------------------------|------------|-----|------------------|-------|
| t_{PHL}, t_{PLH} | Maximum Propagation Delay | | 8 | 15 | ns |

AC Electrical Characteristics $V_{CC}=2.0V\text{ to }6.0V, C_L=50\text{ pF}, t_r=t_f=6\text{ ns}$ (unless otherwise specified)

| Symbol | Parameter | Conditions | V_{CC} | $T_A = 25^{\circ}C$ | | 74HC | 54HC | Units |
|--------------------|--|------------|----------|---------------------|-------------------|-----------------------------------|------------------------------------|-------|
| | | | | | | $T_A = -40\text{ to }85^{\circ}C$ | $T_A = -55\text{ to }125^{\circ}C$ | |
| | | | | Typ | Guaranteed Limits | | | |
| t_{PHL}, t_{PLH} | Maximum Propagation Delay | | 2.0V | 45 | 90 | 113 | 134 | ns |
| | | | 4.5V | 9 | 18 | 23 | 27 | ns |
| | | | 6.0V | 8 | 15 | 19 | 23 | ns |
| t_{TLH}, t_{THL} | Maximum Output Rise and Fall Time | | 2.0V | 30 | 75 | 95 | 110 | ns |
| | | | 4.5V | 8 | 15 | 19 | 22 | ns |
| | | | 6.0V | 7 | 13 | 16 | 19 | ns |
| C_{PD} | Power Dissipation Capacitance (Note 5) | (per gate) | | 20 | | | | pF |
| C_{IN} | Maximum Input Capacitance | | | 5 | 10 | 10 | 10 | pF |

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.